Form PTO-1449 (REV. 8-83)	•	US Dept. of Commerce PATENT & TRADEMARK OFFICE			ATTY DOCKET NO. 108272.01			APPLICATION NO. Rule 53(b) Continuing Application of U.S.		
INFOR	MATI	ION DISCLOSURE STATEMENT	ı		·		Appli	cation No. (9/748,207	
	(Use	several sheets if necessary)		APPLICANT(S) Yoshitaka SASAKI et al.						
: 				FILING DATE March 2, 2004						
U.S. PATENT DOCUMENTS										
EXAMINER INITIAL		DOCUMENT NUMBER		DATE	NAME		CLASS	CLASS		
ДC	1	6,083,410	07/.	2000	Ikegawa et al.		•			
Ac	2	6,333,841	12/:	2001	Sesaki					
AC	3	6,459,551	10/	2002	Hayakawa					
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FOREIGN PATENT DOCUMENTS										
		DOCUMENT NUMBER		DATE	COUNTRY			CLASS	SUB CLASS	
Ac	4	JP A 4-232250	08/	1992	Japan					
AC	5	JP A 9-91618	04/	1997	Japan					
KC	6	JP A 11-353616	12	1999	Japan					
æ	7	JP A 11-39614	12/	1999	Japan			_		
AC	8	WO 99/41739	08/	1999	WIPO					
		OTHER DOCUMENTS (Inc	cludir	ng Author, 7	litle, Date, Pertinent Pages,	, etc.)				
ョン	Ericsson et al.; "Properties of Al ₂ O ₂ -films deposited on silicon by atomic layer epitaxy"; Microelectronic Engineering 36 (1997) 91-94									
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EXAMINER	AMINER Allen los DATE CONSIDERED 1/30/06									
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw tine through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.										

Date: March 2, 2004